

# PERFORMANCE ANALYSIS OF ULTRA LOW POWER MCML BASED VCO DESIGN

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## Abstract

Power has always been a concern due to the adaptation of technology scaling. Power mitigation techniques needs to be adopted. Due to the advancement in VLSI design, the ultra low power designs have acquired a great importance. The subthreshold design has proven to be a boon for ultra low power applications. The paper explores the operation of voltage controlled oscillator design. The VCO is designed using MOS current mode logic style. Further, the performance analysis is carried out and the design is compared with the conventional current starved VCO. It is found that the VCO design provides improved phase noise margin of about -16.2dbc/Hz. The temperature and power supply sensitivity of the design has also been carried out. It is found that the supply sensitivity is reduced to 0.054GHz/V.

**Keywords**—Current starved; Sensitivity.

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## 1. INTRODUCTION

The VLSI design has always played a vital role in the field of digital signal processing, automation, robotics etc. The ultra low power design is the most recent trend in VLSI. Since power reduction the main objective behind adopting the ultra low power design. The ultra low power design exhibits various various characteristics such as high performance, high speed and low power operations. The CMOS technology have always been a boon to the VLSI area. The design of CMOS using MOS current mode logic concept has gained a lot of importance. The operation of MOS current mode design exhibits a lot of importance due to its various advantage over the conventional CMOS. Some of its advantages includes high speed, high performance, and stability. Hence, using such design a voltage controlled oscillator can be designed.

Voltage control oscillator is the main component in various circuitry such as digital circuits, timing circuits, radio receivers, PLL etc. The voltage control oscillator operation depends on various parameters. Some of the parameters are tuning range, phase noise, supply sensitivity etc. These factors decides the performance of the given voltage controlled design. The performance of VCO is degraded due to power supply noise. Ring oscillator is greatly affected by such power supply noise. There are various VCO metrics that gets affected due to noise. Hence, there is a need to design a robust system that can counter balance the variations caused by the power supply noise. There are various techniques that can be adopted in order to reduce supply sensitivity.

A lot of techniques can be adopted like using a D flip flop at the output stage. Some techniques involved designing a VCO along with a source follower instead of dc current

source. This paper depicts a technique of implementing a VCO using mcml logic design with low supply sensitivity as proposed by the author in [20]. Further, the performance analysis is carried out using various VCO design parameters. The VCO design is then compared with the conventional current starved VCO. In section II, MOS current mode logic design technology is explained. In section III, the voltage controlled oscillator design based on MCML is explained. In section IV, the performance comparison is carried out. In section V, the conclusion is drawn out.

## 2. MOS CURRENT MODE LOGIC DESIGN

Fig.1. shows the basic MCML buffer logic style. The current mode logic style consist of driven and the driver elements. The PMOS acts as a linear resistor. The NMOS works as a switch. The switching operation is controlled by the current present in the NMOS which at the tail of the circuit and hence the design is called as MOS current mode design. Such a design enables fast switching operation.

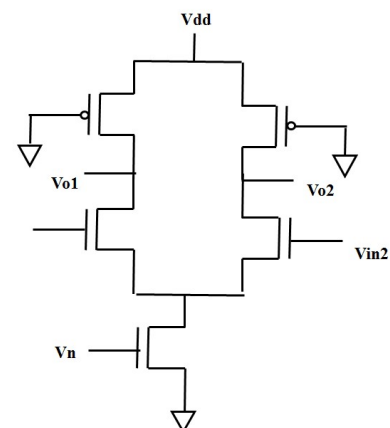


Fig.1. MCML buffer



Fig.3 shows that the tuning range of 4-stage CML ring oscillator. Secondly, the performance of compensated 4-stage ring CML oscillator is evaluated with the addition of power supply noise. Fig.5 shows the tuning range of compensated 4-stage CML ring oscillator. The tuning range of the compensated ring oscillator is obtained by varying the voltage levels of the tail NMOS transistor. The voltages are varied from -200mV to 200mV. This range is the difference of  $v_{c1+}$  and  $v_{c2+}$  so as to get full swing as per CMOS standard voltage level. Fig.4 shows the tuning range plot of compensated CML ring oscillator.

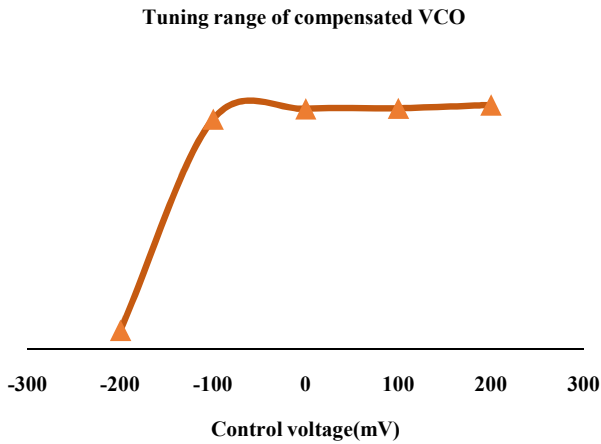


Fig.4 Tuning range of compensated ring

The tuning range is plotted as shown in Fig.4. The tuning range obtained is 1.17-1.1185GHz while the conventional cml ring has only 1.266-1.2754 GHz. Therefore, compensated ring VCO has wide tuning range. Similarly, the sensitivity of both the oscillators has been compared. The performance comparison of both the oscillators is done with the conventional current starved ring oscillator. Further, the variation of frequency with temperature is examined and is tabulated in Table I. Similarly, the comparison of phase noise of both the VCOs was done at an offset of 10MHz. The phase noise plot for CML VCO is as shown in Fig.5 a) and the phase noise plot for compensated CML VCO is plotted in Fig.5 b).

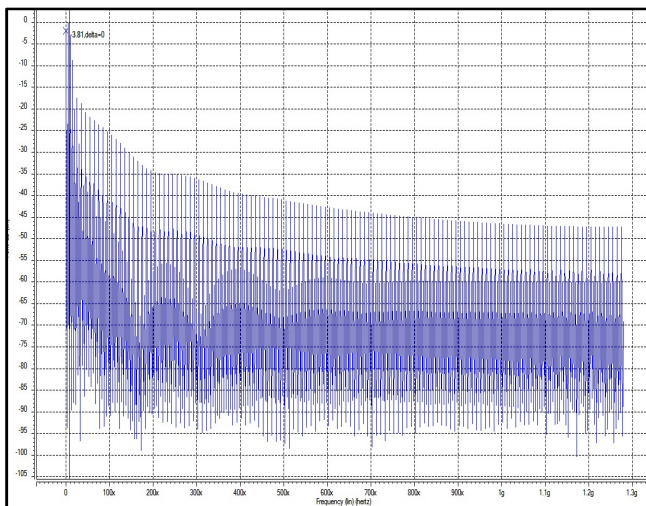


Fig.5 Phase noise plot for a) CML ring VCO

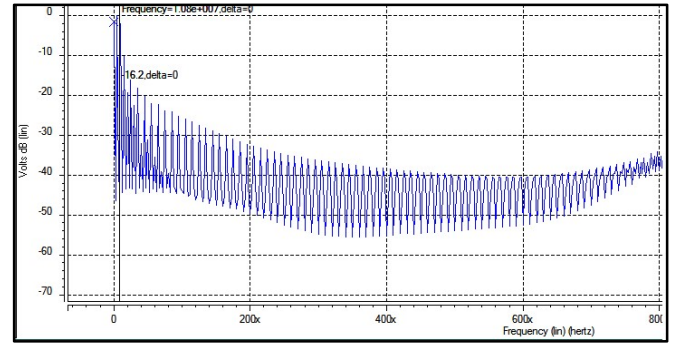


Fig.6 Phase noise plot for a) compensated VCO

The compensated phase noise is about -16.2dbc/Hz at an offset of 10MHz. While, the phase noise of the CML VCO is about -3.81dbc/Hz. Next, the temperature sensitivity and supply sensitivity of both the VCO were compared with the conventional current starved CMOS ring VCO. Fig.7 shows the comparison of temperature sensitivity of the CML ring, compensated VCO and the current starved VCO.

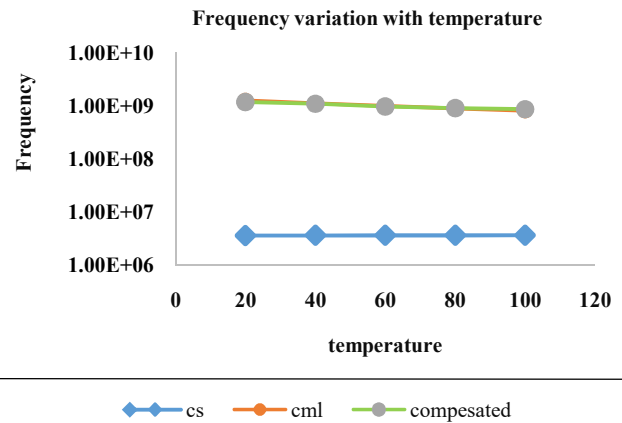


Fig.7 shows the plot of temperature sensitivity of CML ring, compensated ring and current starved VCO.

It is found that the temperature sensitivity of CML ring and compensated is almost same. The temperature variation is tabulated in table I

Table 1: Comparison Of Frequency Variation With Temperature Of Vcos

Temperature	CML ring(GHz)	Compensated (GHz)	Current starved (MHz)
20	1.266	1.1794	3.628
40	1.1252	1.105	3.63
60	1.00	0.9739	3.649
80	0.9004	0.907	3.65
100	0.818	0.874	3.681

The temperature variation in CML ring is about 35% while that in compensated CML VCO is reduced to about 25.8%. Further, the supply voltage was varied and the sensitivity was calculated for all three designs. Fig.8. shows the plot of supply sensitivity comparison.

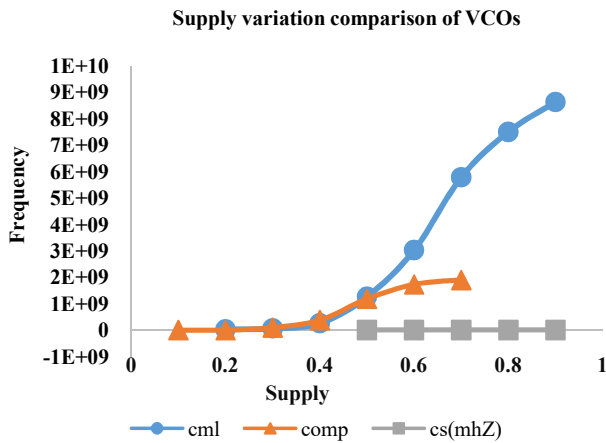


Fig.8 shows the plot of supply sensitivity of CML ring, compensated ring and current starved VCO.

The CML ring VCO is highly susceptible to the supply variation. The supply sensitivity calculated is about 0.176GHz/V. The compensated VCO has low sensitivity of about 0.054GHz/V. The performance comparison is carried out and tabulated in table II.

Table 2: Performance Comparison Of CML Ring, Compensated Ring And Current Starved Ring Oscillators.

Parameter	Current starved	CML ring VCO	Compensated VCO[20]
$f_{osc}$	3.63MHz	1.266GHz	1.17GHz
Average power	2.3169uW	0.588mW	0.17682mW
Tuning sensitivity	0.38MHz/V	0.74GHz/V	0.85GHz
Tuning range	3.627-3.628MHz	1.266-1.27GHz	1.17-1.118GHz
Phase noise	-15.4dbc/Hz	-3.81dbc/Hz	-16.2dbc/Hz
Supply sensitivity	0.013MHz/V	0.176GHz/v	0.0546GHz/V
Temperature variation	1.4%	35.38%	25.8%

The performance comparison table shows that the tuning range of the compensated 4-stage CML ring oscillator is more as compared to the conventional current starved oscillator. The tuning range obtained for 4-stage CML ring oscillator is only 1.266-1.275GHz. The current starved provides a tuning range of 3.6275-3.6283MHz. The supply sensitivity of 4-stage CML ring is 0.176GHz/V and for current starved it is about 0.013MHz/V. This compensation circuit stage provides a low supply sensitivity as compared to the CML ring oscillator. The supply sensitivity obtained is about 0.0546GHz/V. The compensated 4-stage oscillator provides low sensitivity to supply variation while maintaining same oscillatory frequency. The average power is also low of about 0.17682mW for the compensated VCO than CML ring VCO.

The variability is an issue in the design of various technology. The three main component for variability are

process, voltage and temperature. When the CMOS is scaled, the effect called random dopant fluctuation is caused. This affects the threshold voltage and voltage swing. Eventually, this causes changes in voltage rise and fall time. This variation causes fluctuation in frequency. Hence, there is a need to encounter this problem. The variability test of the VCO was investigated under PVT variation. The parameters were varied and the effect of PVT variation on the frequency of the VCOs was studied. The probability density function was plotted for all the VCOs and compared. Monte Carlo analysis was carried out for 30 runs and variation in the frequency was noted.

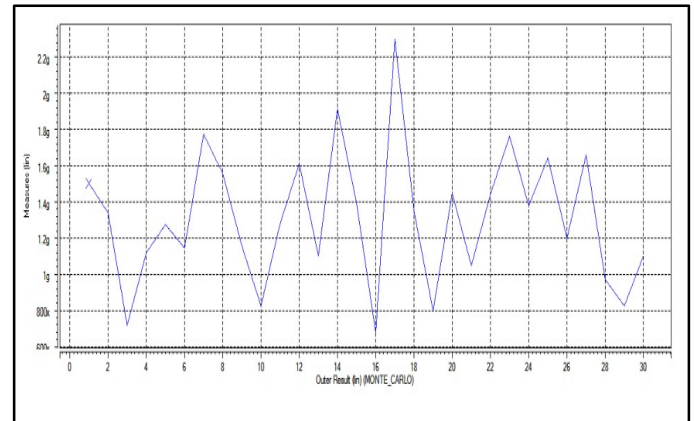


Fig.9 Variation in frequency for 30 runs for CML ring VCO.

Fig.9 shows the variation in frequency for 30 runs using Monte Carlo simulation and it was found that frequency varies from 600MHz-2.2GHz. The variation in frequency is about 1.6GHz for CML VCO.

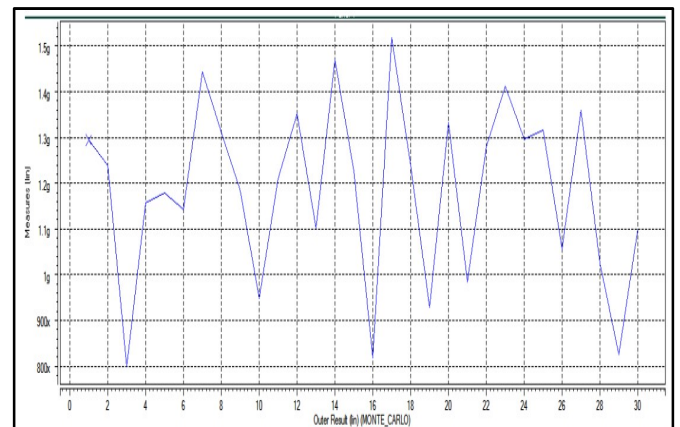
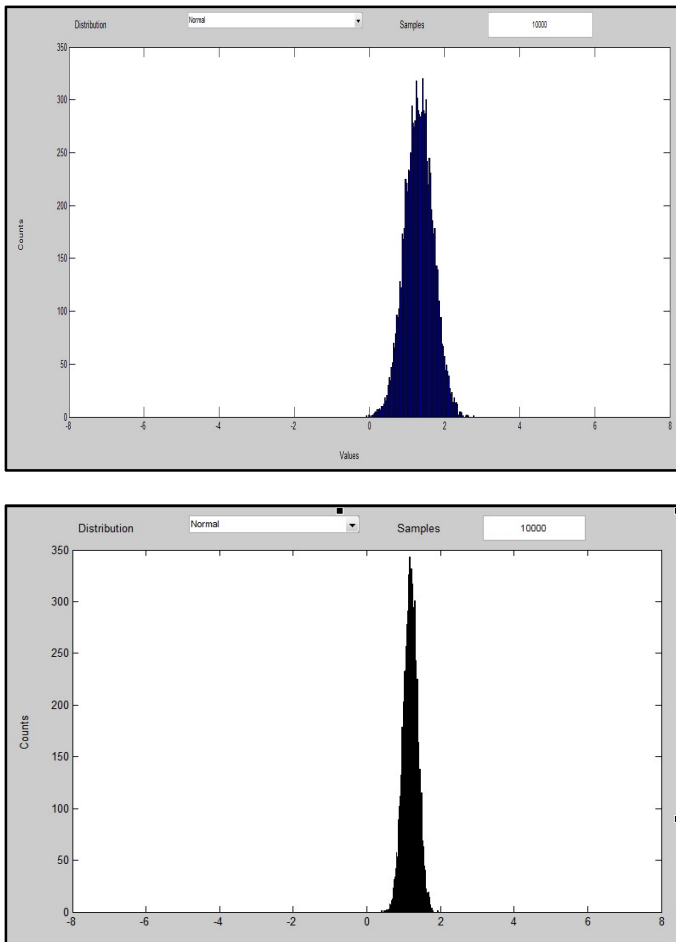


Fig.10 Variation in frequency for 30 runs of CML ring compensated VCO

Fig.10 shows the variation in frequency for 30 runs using Monte Carlo simulation and it was found that frequency varies from 800MHz-1.5GHz. The variation in frequency is about 0.7GHz. Further, the probability distribution for frequency was plotted and investigated as shown in Fig.10. The table III depicts the comparison of mean, variance and coefficient of variation for current starved, CML ring and compensated VCO. The coefficient of variation should be as low as possible. The coefficient of variation signifies the ratio of variance to the mean.



**Fig.11** Probability density function for frequency for a) CML VCO and b) Compensated VCO

The probability density function for frequency indicates that the frequency is tightly clustered for the compensated VCO with mean=1.1875. The frequency function is loosely clustered for CML ring VCO at mean=1.311. Also, for the current starved the frequency is tightly clustered with the least coefficient of variation. The comparison of mean, variance and coefficient of variation is tabulated in table III.

**Table 3:** Variability Test

Parameter	Current starved	CML ring VCO	Compensated VCO
mean( $\mu$ )	3641.1	1.311	1.1875
Sigma( $\sigma$ )	98.3	0.375	0.194
Coefficient of variation(CV)	0.026	0.28	0.163

The coefficient of variation is also called as relative standard deviation. It is defined as the standard measure of dispersion for the probability distribution. The coefficient of variation is minimum for the current starved VCO and it is about 0.0546.

The coefficient of variation is less for compensated than the CML VCO ring.

## 5. CONCLUSION

The phase noise of the compensated system obtained is -16.2dbc/Hz. The compensated system has low supply sensitivity of about 0.0546GHz/V than conventional current starved as well as conventional ring oscillator while maintaining nearly constant oscillatory frequency. The tuning range is also improved than conventional CML ring oscillator. Its average power is also low. Further, the analysis shows that compensated VCO is more stable for temperature variation and supply sensitivity. The coefficient of variation obtained is 0.163.

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